

## **REMARKS**

Claims 1, 24-26, 40, 41 and 68 are amended. Claims 1-68 are in the application for consideration.

The claims are amended in a manner which in no way goes to patentability, nor changes the scope of the amended claims. Specifically, claims 1, 24-26, 40, 41 and 68 are amended to insert more grammatically correct and preferred hyphenation. No change in meaning or scope occurs thereby.

Further, independent claims 1 and 41 are amended to recite the more grammatically preferred "depositing a crystalline form layer comprising at least one of TiN, WN, elemental form W, or SiC". No change in meaning or scope occurs thereby.

Claims 16-19 and 51-54 are rejected as failing to further limit the subject matter of a previous claim. Applicant disagrees and requests reconsideration.

Applicant's independent claims 1 and 41 recite the depositing of a crystalline form layer which comprises at least one of four stated materials. Accordingly, independent claims 1 and 41 do not require the inclusion of all of the stated materials. The dependent claims objected to merely individually recite/require specific ones of the four stated materials, and therefore do further limit the subject of the independent claim from which such depends. Accordingly, the Examiner's claim objection in this regard should be withdrawn, and action to that end is requested.

A Supplemental Information Disclosure Statement is filed herewith.

This application is believed to be in immediate condition for allowance,  
and action to that end is requested.

Respectfully submitted,

Dated: 6-7-05

By: 

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